NSN 5962-01-351-4989

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nanoseconds propagation delay time, low to high level

View Online at https://aerobasegroup.com/nsn/5962-01-351-4989

New Online at https://aeiobasegroup.com/hsil/3902-01-331-4909
Overall Length:
1.280 inches
Overall Height:
0.400 inches
Body Length:
1.280 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Satellite communications terminal an/usc-3 (v) 1
Features Provided:
High impedance and w/clock and programmed and bipolar and monolithic and bidirectional
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
20 input
Case Outline Source And Designator:
D-9 mil-m-38510
Current Rating Per Characteristic:
165.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
35.00 nanoseconds propagation delay time, high to low level output and 35.00 nanosecond
output
Memory Device Type:

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Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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